What Is Claimed Is:

1	 A split gate flash memory, comprising:
2	a substrate with a trench therein;
3	a drain in the bottom of the trench;
4	a source in the substrate outside the trench;
-	a striped floating gate disposed at a sidewall of the
5	trench, wherein one side of the striped floating gate is near
6	the bottom of the trench, and the other side of the striped
7	the bottom of the trench, and the tracks
8	floating gate protrudes above the substrate;
9	a control gate winding along the floating gate, wherein
10	one side of the control gate is near the bottom of the trench,
10	and the other side of the control gate in outside the trench;
11	and the other side of the constants
12	and
13	a metal bit line connected to the drain.
1	2. The split gate flash memory as claimed in claim 1, further
2	comprising an oxide layer surrounding the striped floating gate,
3	the control gate and the substrate.